

1N6373 - 1N6381 Series (ICTE-5 - ICTE-36)

1500 Watt Peak Power Mosorb™ Zener Transient Voltage Suppressors

Unidirectional*

Mosorb devices are designed to protect voltage sensitive components from high voltage, high-energy transients. They have excellent clamping capability, high surge capability, low zener impedance and fast response time. These devices are ON Semiconductor's exclusive, cost-effective, highly reliable Surmetic™ axial leaded package and are ideally-suited for use in communication systems, numerical controls, process controls, medical equipment, business machines, power supplies and many other industrial/consumer applications, to protect CMOS, MOS and Bipolar integrated circuits.

Specification Features

- Working Peak Reverse Voltage Range - 5.0 V to 45 V
- Peak Power - 1500 Watts @ 1 ms
- ESD Rating of Class 3 (>16 KV) per Human Body Model
- Maximum Clamp Voltage @ Peak Pulse Current
- Low Leakage < 5 μ A Above 10 V
- Response Time is Typically < 1 ns
- Pb-Free Packages are Available*

Mechanical Characteristics

CASE: Void-free, transfer-molded, thermosetting plastic

FINISH: All external surfaces are corrosion resistant and leads are readily solderable

MAXIMUM LEAD TEMPERATURE FOR SOLDERING PURPOSES: 260°C, 1/16" from the case for 10 seconds

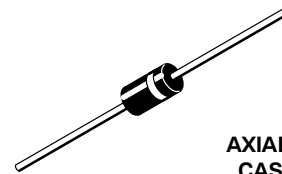
POLARITY: Cathode indicated by polarity band

MOUNTING POSITION: Any



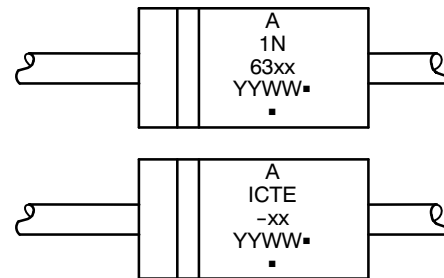
ON Semiconductor®

<http://onsemi.com>



AXIAL LEAD
CASE 41A
PLASTIC

MARKING DIAGRAMS



- A = Assembly Location
 - 1N63xx = JEDEC Device Code
 - ICTE-xx = ON Device Code
 - YY = Year
 - WW = Work Week
 - = Pb-Free Package
- (Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
1N63xx, G	Axial Lead (Pb-Free)	500 Units/Box
1N63xxRL4, G	Axial Lead (Pb-Free)	1500/Tape & Reel
ICTE-xx, G	Axial Lead (Pb-Free)	500 Units/Box
ICTE-xxRL4, G	Axial Lead (Pb-Free)	1500/Tape & Reel

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

1N6373 – 1N6381 Series (ICTE-5 – ICTE-36)

MAXIMUM RATINGS

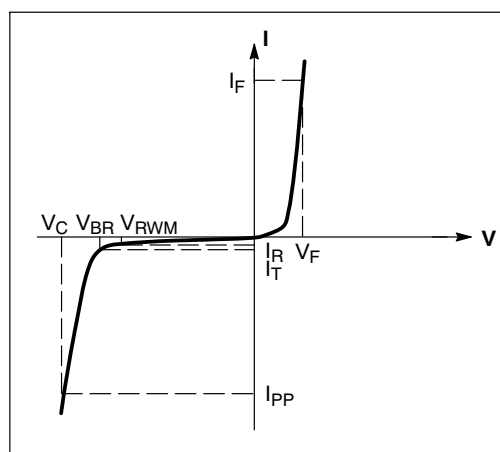
Rating	Symbol	Value	Unit
Peak Power Dissipation (Note 1) @ $T_L \leq 25^\circ\text{C}$	P_{PK}	1500	W
Steady State Power Dissipation @ $T_L \leq 75^\circ\text{C}$, Lead Length = 3/8" Derated above $T_L = 75^\circ\text{C}$	P_D	5.0 20	W mW/°C
Thermal Resistance, Junction-to-Lead	$R_{\theta JL}$	20	°C/W
Forward Surge Current (Note 2) @ $T_A = 25^\circ\text{C}$	I_{FSM}	200	A
Operating and Storage Temperature Range	T_J, T_{stg}	- 65 to +175	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Nonrepetitive current pulse per Figure 5 and derated above $T_A = 25^\circ\text{C}$ per Figure 2.
2. 1/2 sine wave (or equivalent square wave), $PW = 8.3$ ms, duty cycle = 4 pulses per minute maximum.

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted, $V_F = 3.5$ V Max. @ I_F (Note 3) = 100 A)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
ΘV_{BR}	Maximum Temperature Variation of V_{BR}
I_F	Forward Current
V_F	Forward Voltage @ I_F



Uni-Directional TVS

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted, $V_F = 3.5$ V Max. @ I_F (Note 3) = 100 A)

JEDEC Device† (ON Device)	Device Marking	V_{RWM} (Note 4) (Volts)	I_R @ V_{RWM} (μA)	Breakdown Voltage			V_C @ I_{PP} (Note 6)		V_C (Volts) (Note 6)		ΘV_{BR} (mV/°C)	
				V_{BR} (Note 5) (Volts)			V_C	I_{PP}	@ $I_{PP} = 1$ A	@ $I_{PP} = 10$ A		
				Min	Nom	Max						@ I_T (mA)
1N6373, G	1N6373	5.0	300	6.0	-	-	1.0	9.4	160	7.1	7.5	4.0
1N6374, G	1N6374	8.0	25	9.4	-	-	1.0	15	100	11.3	11.5	8.0
1N6375, G	1N6375	10	2.0	11.7	-	-	1.0	16.7	90	13.7	14.1	12
1N6376, G	1N6376	12	2.0	14.1	-	-	1.0	21.2	70	16.1	16.5	14
1N6377, G	1N6377	15	2.0	17.6	-	-	1.0	25	60	20.1	20.6	18
1N6380, G	1N6380	36	2.0	42.4	-	-	1.0	65.2	23	50.6	54.3	50
1N6381, G	1N6381	45	2.0	52.9	-	-	1.0	78.9	19	63.3	70	60
ICTE-5RLG	ICTE-5	5.0	300	6.0	-	-	1.0	9.4	160	7.1	7.5	4.0
ICTE-10RLG	ICTE-10	10	2.0	11.7	-	-	1.0	16.7	90	13.7	14.1	8.0
ICTE-12RLG	ICTE-12	12	2.0	14.1	-	-	1.0	21.2	70	16.1	16.5	12
ICTE-15RLG	ICTE-15	15	2.0	17.6	-	-	1.0	25	60	20.1	20.6	14
ICTE-18, G	ICTE-18	18	2.0	21.2	-	-	1.0	30	50	24.2	25.2	18
ICTE-36RLG	ICTE-36	36	2.0	42.4	-	-	1.0	65.2	23	50.6	54.3	26

3. Square waveform, $PW = 8.3$ ms, non-repetitive duty cycle.
 4. A transient suppressor is normally selected according to the maximum working peak reverse voltage (V_{RWM}), which should be equal to or greater than the dc or continuous peak operating voltage level.
 5. V_{BR} measured at pulse test current I_T at an ambient temperature of 25°C and minimum voltage in V_{BR} is to be controlled.
 6. Surge current waveform per Figure 5 and derate per Figures 1 and 2.
- †The "G" suffix indicates Pb-Free package or Pb-Free packages are available.

1N6373 - 1N6381 Series (ICTE-5 - ICTE-36)

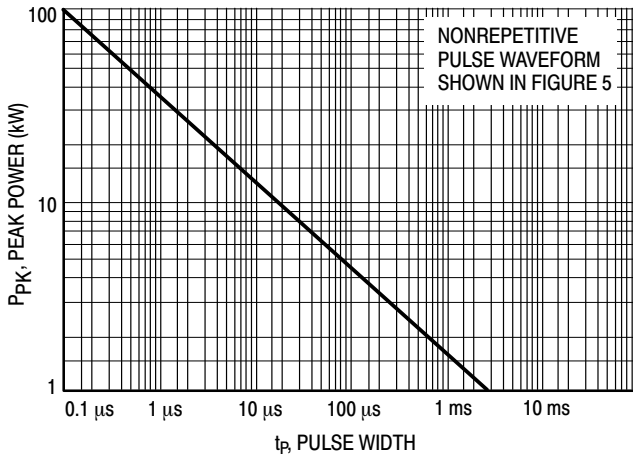


Figure 1. Pulse Rating Curve

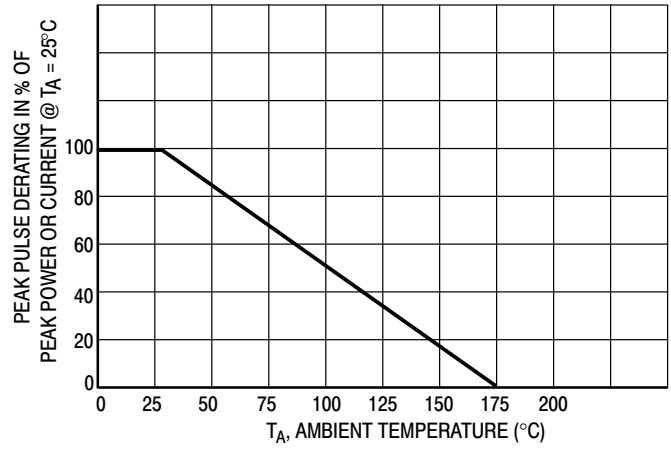


Figure 2. Pulse Derating Curve

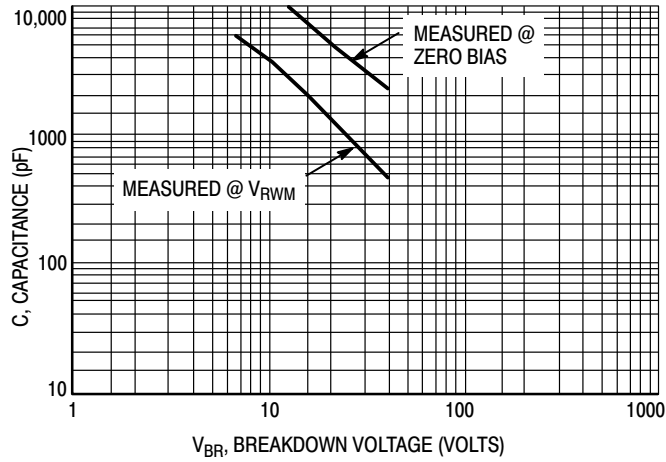


Figure 3. Capacitance versus Breakdown Voltage

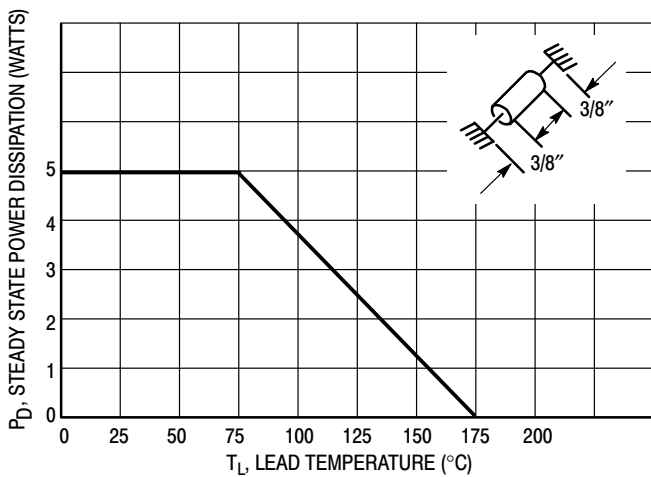


Figure 4. Steady State Power Derating

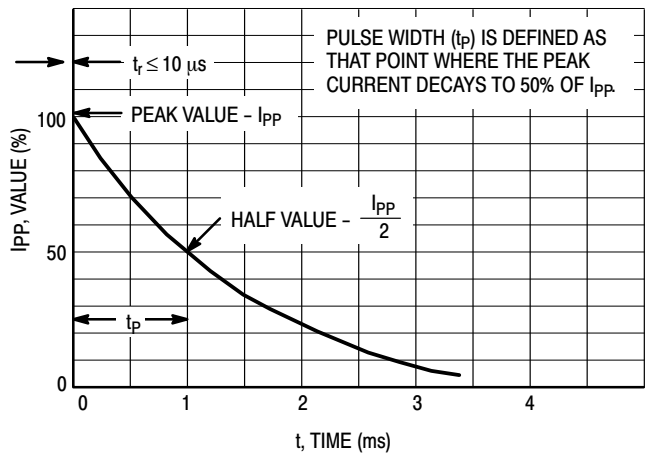


Figure 5. Pulse Waveform

1N6373 - 1N6381 Series (ICTE-5 - ICTE-36)

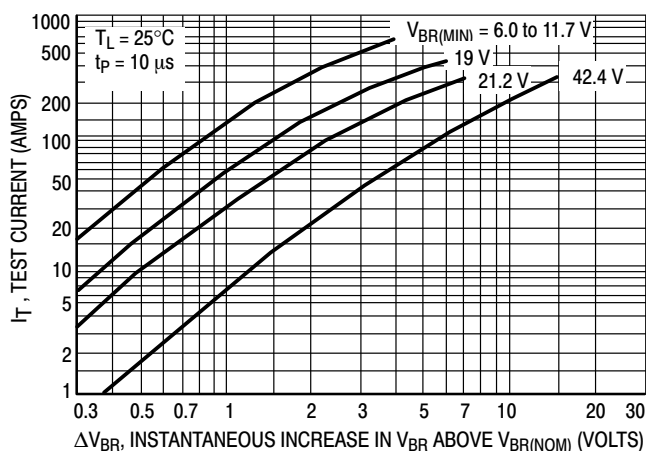


Figure 6. Dynamic Impedance

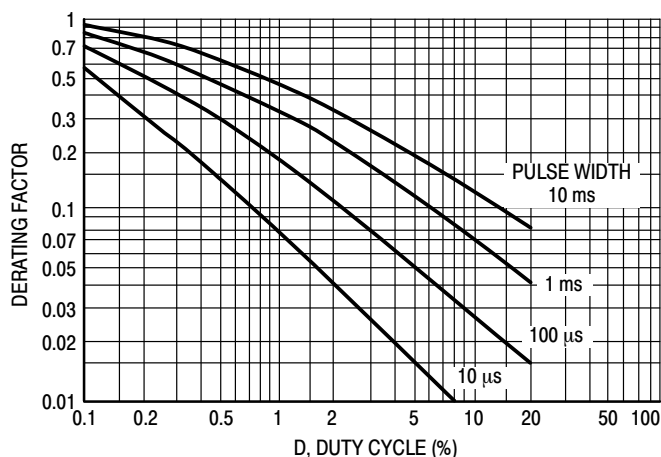


Figure 7. Typical Derating Factor for Duty Cycle

APPLICATION NOTES

RESPONSE TIME

In most applications, the transient suppressor device is placed in parallel with the equipment or component to be protected. In this situation, there is a time delay associated with the capacitance of the device and an overshoot condition associated with the inductance of the device and the inductance of the connection method. The capacitance effect is of minor importance in the parallel protection scheme because it only produces a time delay in the transition from the operating voltage to the clamp voltage as shown in Figure 8.

The inductive effects in the device are due to actual turn-on time (time required for the device to go from zero current to full current) and lead inductance. This inductive effect produces an overshoot in the voltage across the equipment or component being protected as shown in Figure 9. Minimizing this overshoot is very important in the application, since the main purpose for adding a transient suppressor is to clamp voltage spikes. These devices have excellent response time, typically in the picosecond range and negligible inductance. However, external inductive effects could produce unacceptable overshoot. Proper

circuit layout, minimum lead lengths and placing the suppressor device as close as possible to the equipment or components to be protected will minimize this overshoot.

Some input impedance represented by Z_{in} is essential to prevent overstress of the protection device. This impedance should be as high as possible, without restricting the circuit operation.

DUTY CYCLE DERATING

The data of Figure 1 applies for non-repetitive conditions and at a lead temperature of 25°C. If the duty cycle increases, the peak power must be reduced as indicated by the curves of Figure 7. Average power must be derated as the lead or ambient temperature rises above 25°C. The average power derating curve normally given on data sheets may be normalized and used for this purpose.

At first glance the derating curves of Figure 7 appear to be in error as the 10 ms pulse has a higher derating factor than the 10 μs pulse. However, when the derating factor for a given pulse of Figure 7 is multiplied by the peak power value of Figure 1 for the same pulse, the results follow the expected trend.

TYPICAL PROTECTION CIRCUIT

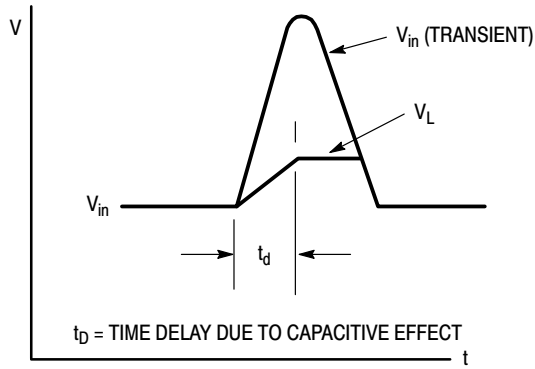
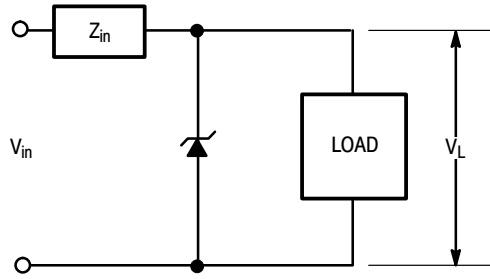


Figure 8.

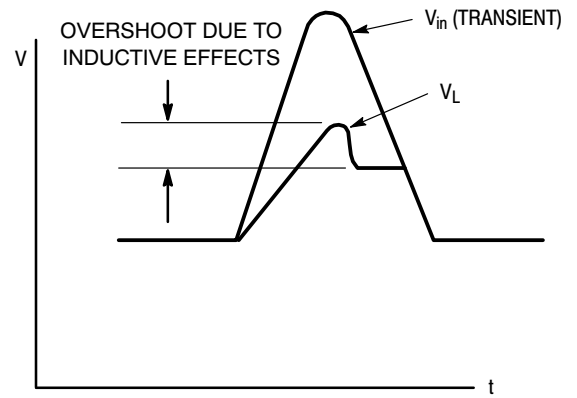
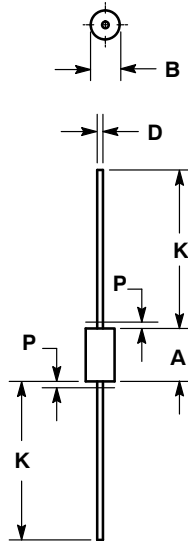


Figure 9.

1N6373 – 1N6381 Series (ICTE-5 – ICTE-36)

PACKAGE DIMENSIONS

MOSORB CASE 41A-04 ISSUE D



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. LEAD FINISH AND DIAMETER UNCONTROLLED IN DIMENSION P.
4. 041A-01 THRU 041A-03 OBSOLETE, NEW STANDARD 041A-04.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.335	0.374	8.50	9.50
B	0.189	0.209	4.80	5.30
D	0.038	0.042	0.96	1.06
K	1.000	---	25.40	---
P	---	0.050	---	1.27

Mosorb and Surmetic are trademarks of Semiconductor Components Industries, LLC.

ON Semiconductor and **ON** are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81-3-5773-3850

ON Semiconductor Website: www.onsemi.com
Order Literature: <http://www.onsemi.com/orderlit>
For additional information, please contact your local Sales Representative

Looking for pricing, stock, or lifecycle information?

Click below to explore more details on WIN SOURCE:

 [View 1N6373RL4G on WIN SOURCE](#)

 [Littelfuse Inc. Information](#)

Optimize Your Supply Chain with WIN SOURCE Solutions

-  Global Sourcing Solution
-  Obsolete Management
-  Cost Control Management
-  Shortage Management
-  Alternative Solution
-  Excess Inventory Management